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(54) **BYPASS DIODE FOR A SOLAR CELL**

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See application file for complete search history.

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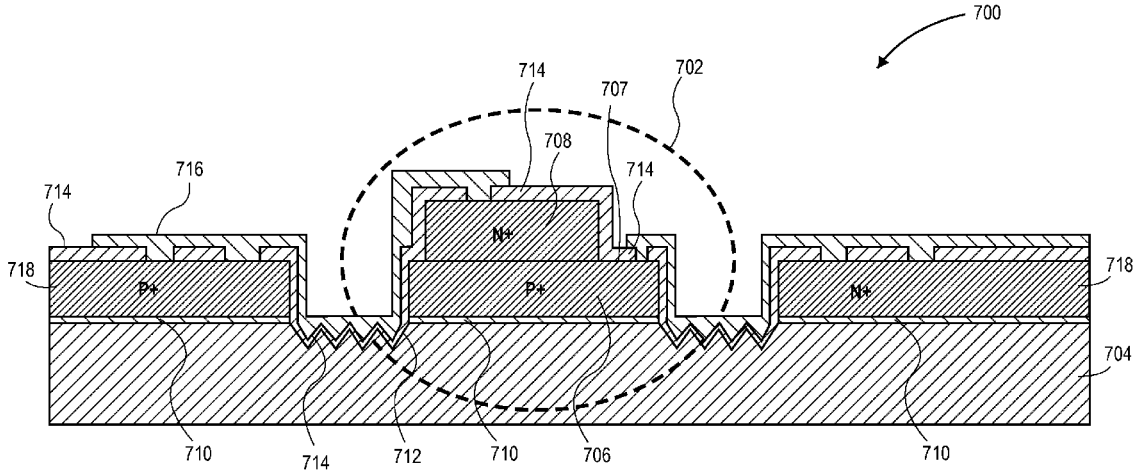
(57) **ABSTRACT**

Bypass diodes for solar cells are described. In one embodiment, a bypass diode for a solar cell includes a substrate of the solar cell. A first conductive region is disposed above the substrate, the first conductive region of a first conductivity type. A second conductive region is disposed on the first conductive region, the second conductive region of a second conductivity type opposite the first conductivity type.

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